

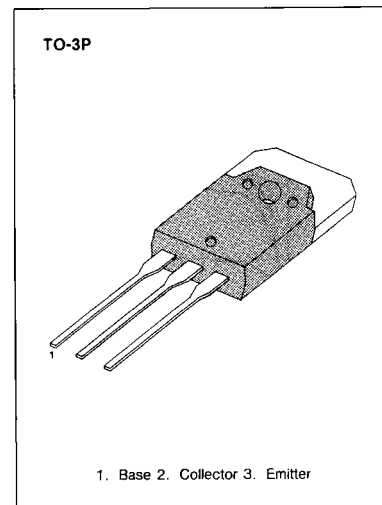
PNP Transistor KSB817 datasheet

AUDIO POWER AMPLIFIER DC TO DC CONVERTER

- High Current Capability
- High Power Dissipation
- Complementary to KSD1047

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V _{CB0}	- 160	V
Collector Emitter Voltage	V _{CE0}	- 140	V
Emitter Base Voltage	V _{EBO}	- 6	V
Collector Current (DC)	I _C	- 12	A
Collector Current (Pulse)	I _C	- 15	A
Collector Dissipation	P _C	100	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	- 40 ~ 150	°C



ELECTRICAL CHARACTERISTICS (T_A = 25°C)

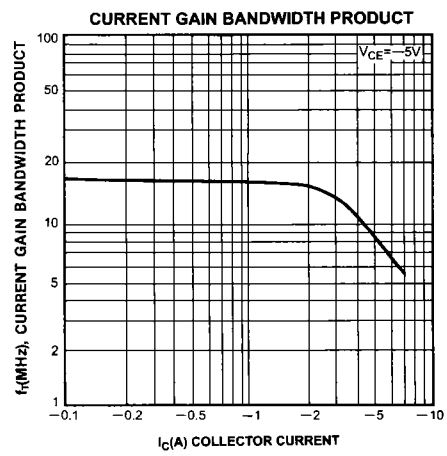
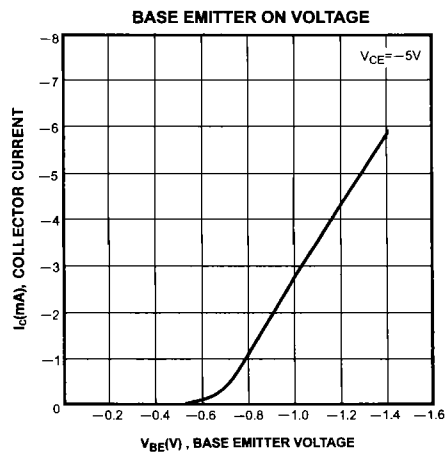
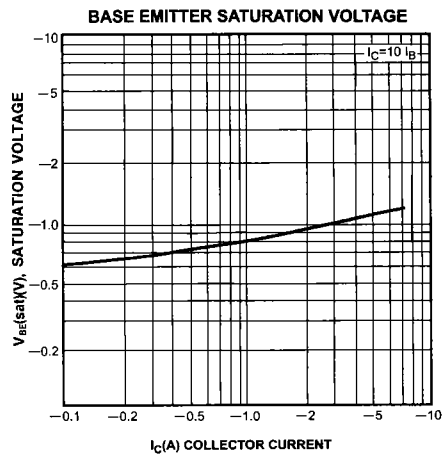
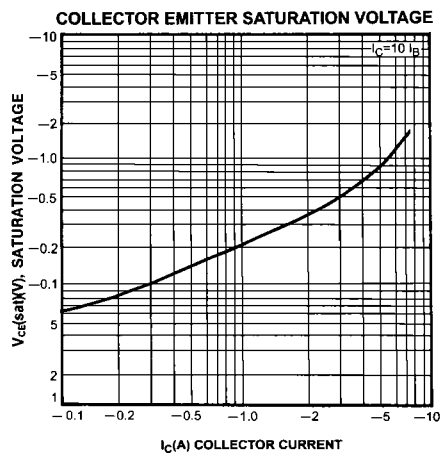
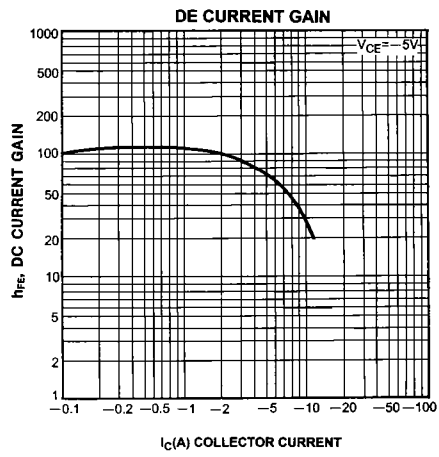
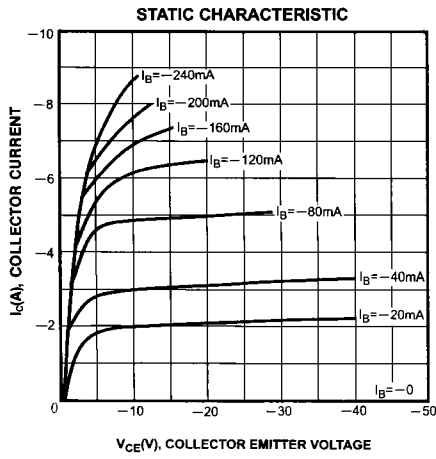
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV _{CB0}	I _C = - 5mA, I _E = 0	- 160			V
Collector Emitter Breakdown Voltage	BV _{CE0}	I _C = - 10mA, R _{BE} = ∞	- 140			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E = - 5mA, I _C = 0	- 6			V
Collector Cutoff Current	I _{CB0}	V _{CB} = - 80V, I _E = 0			- 0.1	mA
Emitter Cutoff Current	I _{EBO}	V _{BE} = - 4V, I _C = 0			- 0.1	mA
*DC Current Gain	h _{FE1}	V _{CE} = - 5V, I _C = - 1A	60		200	
	h _{FE2}	V _{CE} = - 5V, I _C = - 6A	20			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = - 5A, I _B = - 0.5A			- 2.5	V
Base Emitter On Voltage	V _{BE(On)}	I _{CE} = - 5V, I _C = - 1A			- 1.5	V
Current Gain Bandwidth Product	f _T	V _{CE} = - 5V, I _C = - 1A		15		MHZ
Output Capacitance	C _{ob}	V _{CB} = - 10V, f = 1MHZ		300		pF
Turn On Time	t _{on}	V _{CC} = 20V		0.25		us
Fall Time	t _f	I _C = 1A = 10 · I _{B1} = - 10 · I _{B2} ,		0.53		us
Storage Time	t _{stg}	R _L = 20Ω		1.61		us

* Plus test: PW = 20μs

* h_{FE}(1) CLASSIFICATION

Classification	O	Y
h _{FE} (1)	60~120	100~200

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